

Figure 1

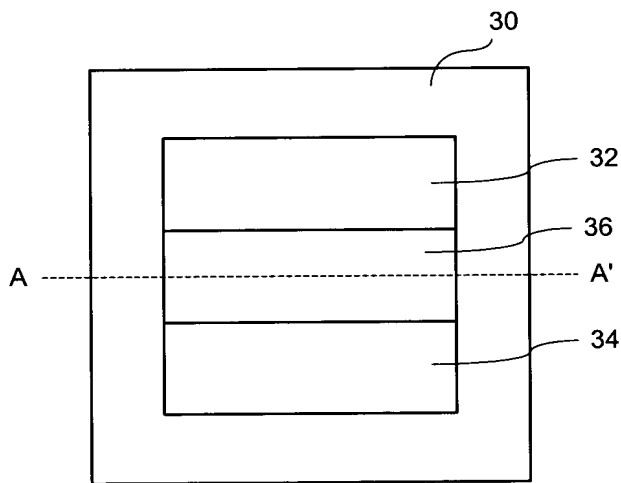


Figure 2a

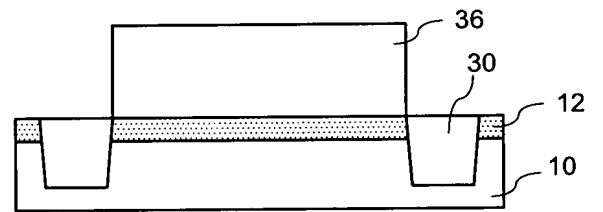


Figure 2b

Figure 2c

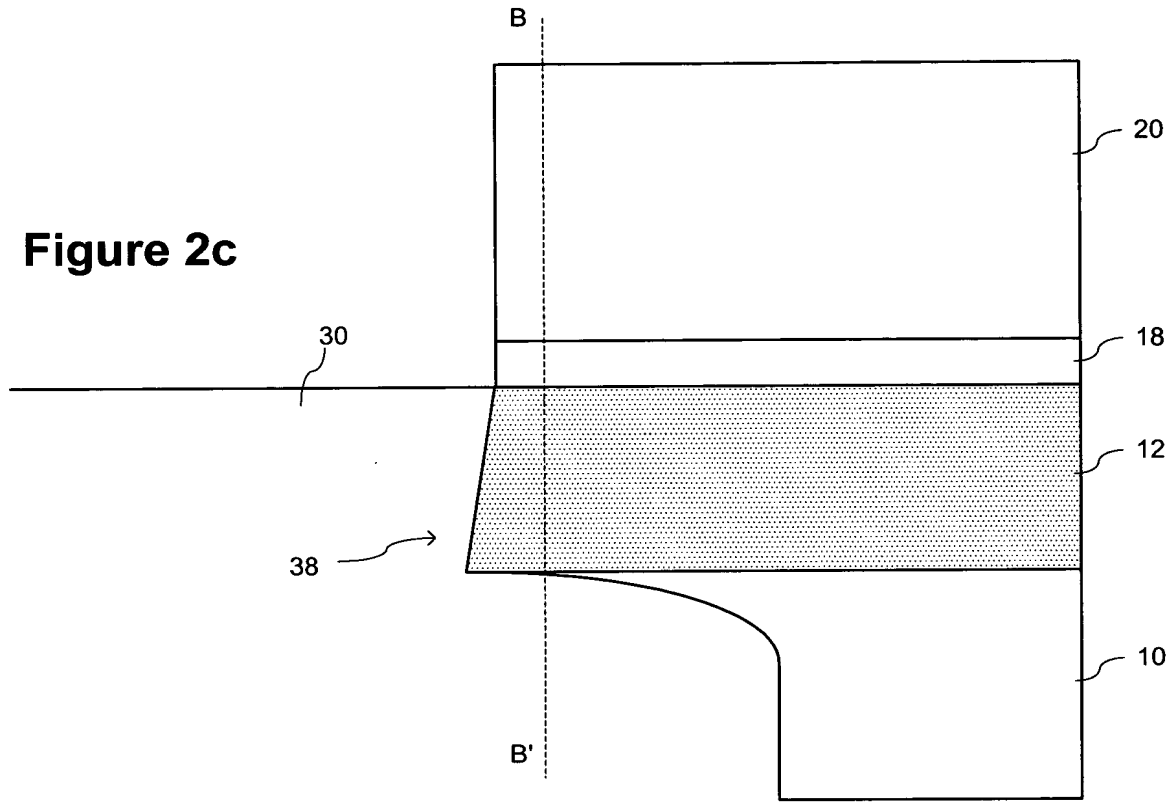
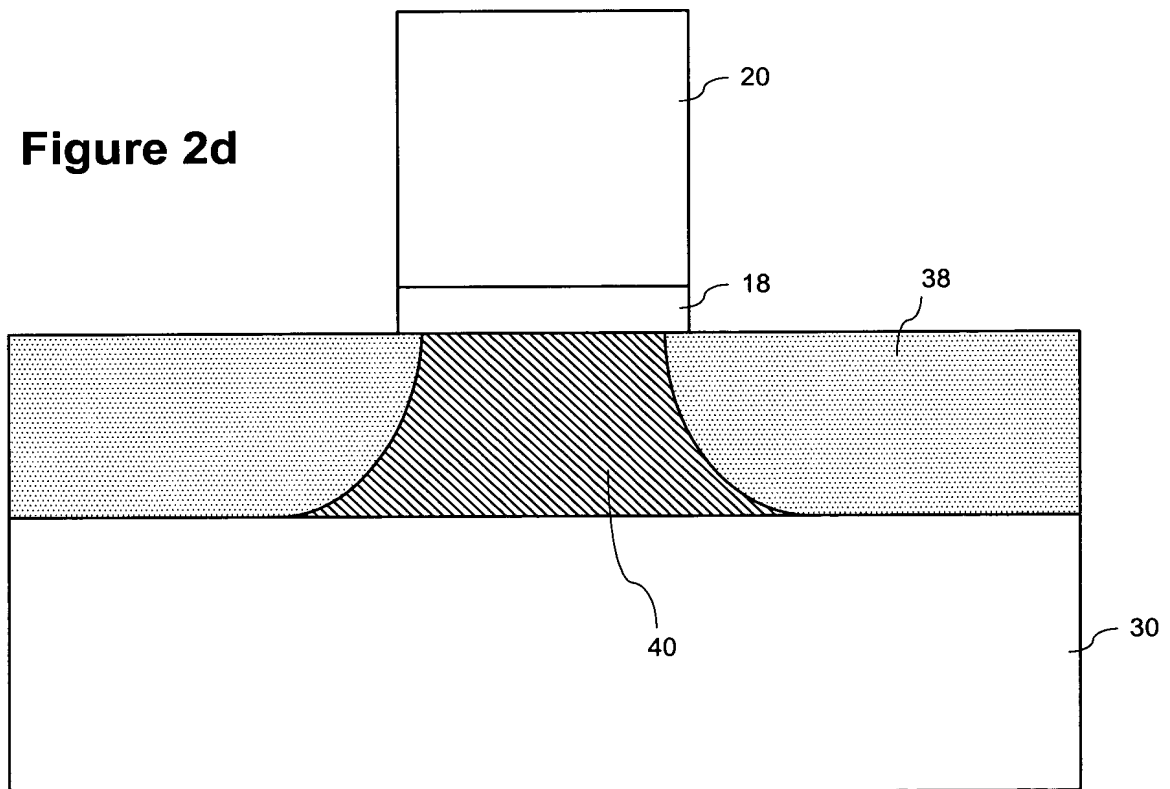


Figure 2d



STRAINED SILICON MOSFET HAVING
REDUCED LEAKAGE AND METHOD OF ITS
FORMATION

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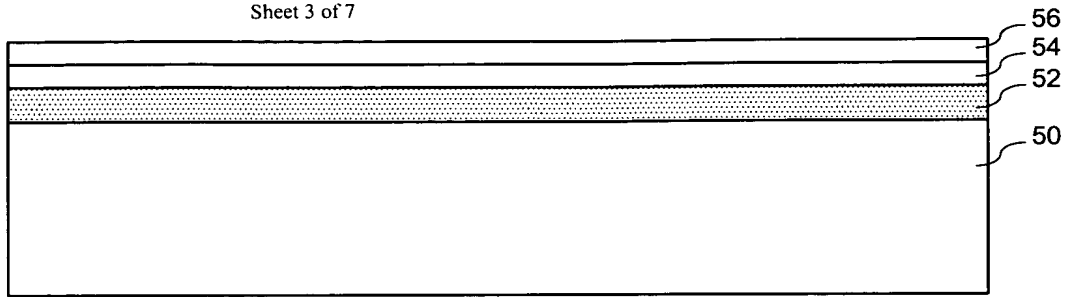


Figure 3a

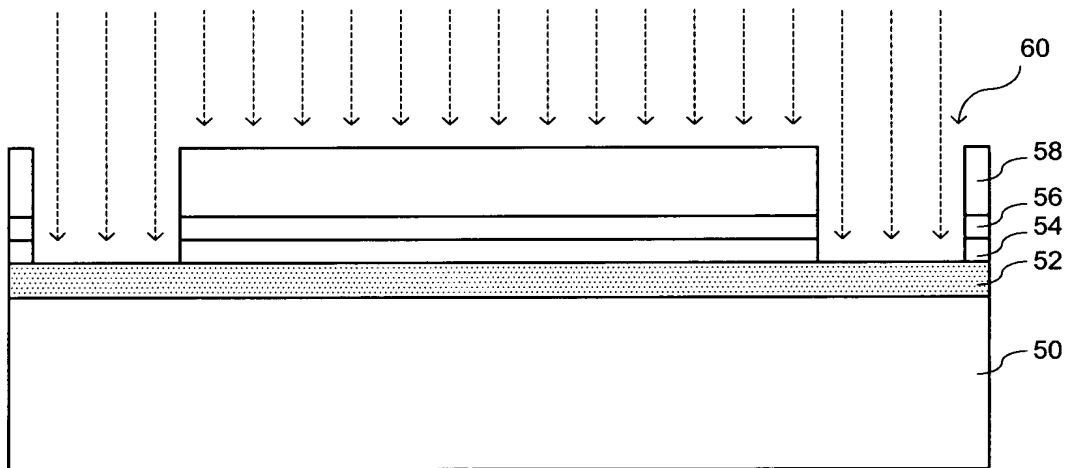


Figure 3b

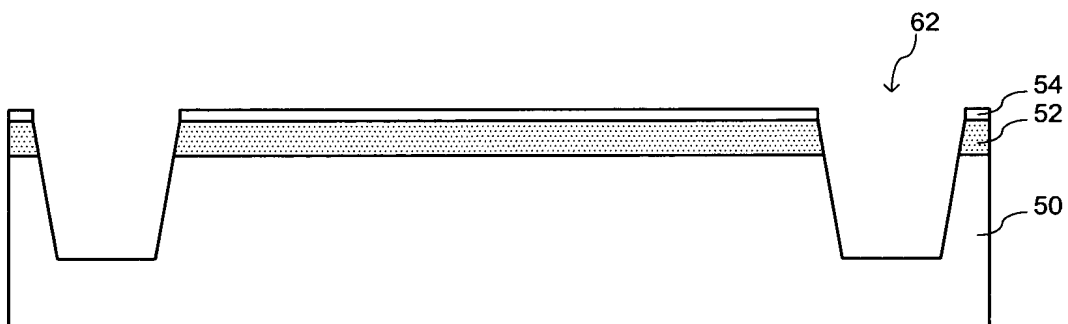


Figure 3c

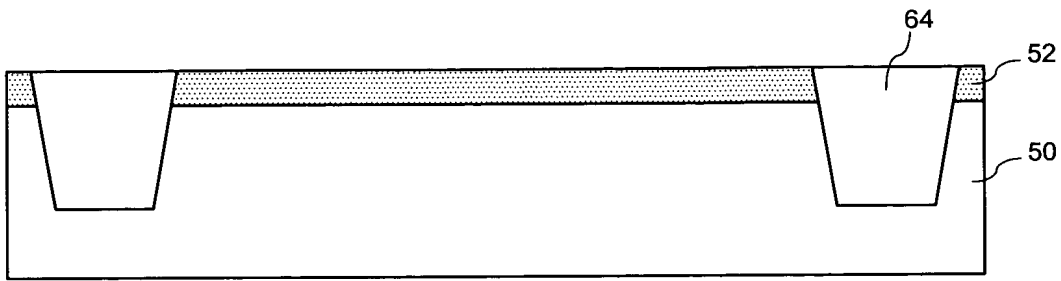


Figure 3d

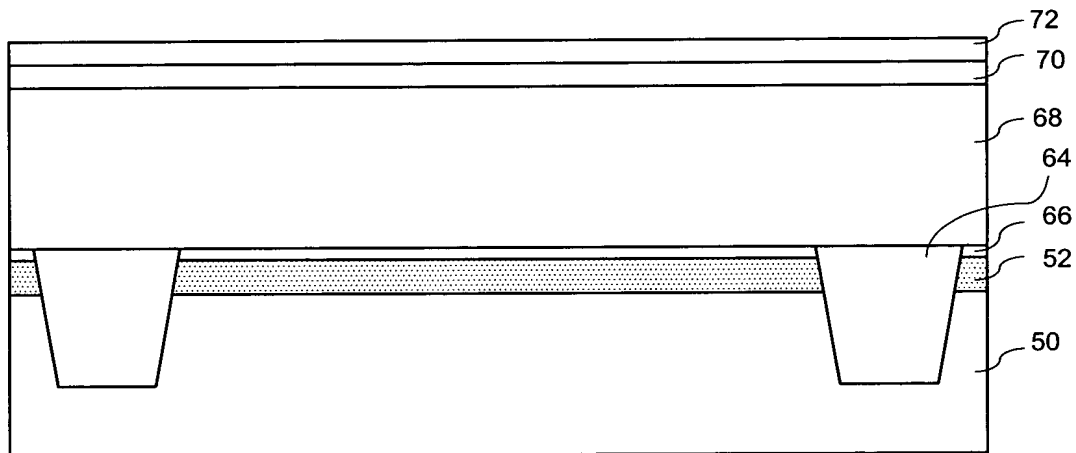


Figure 3e

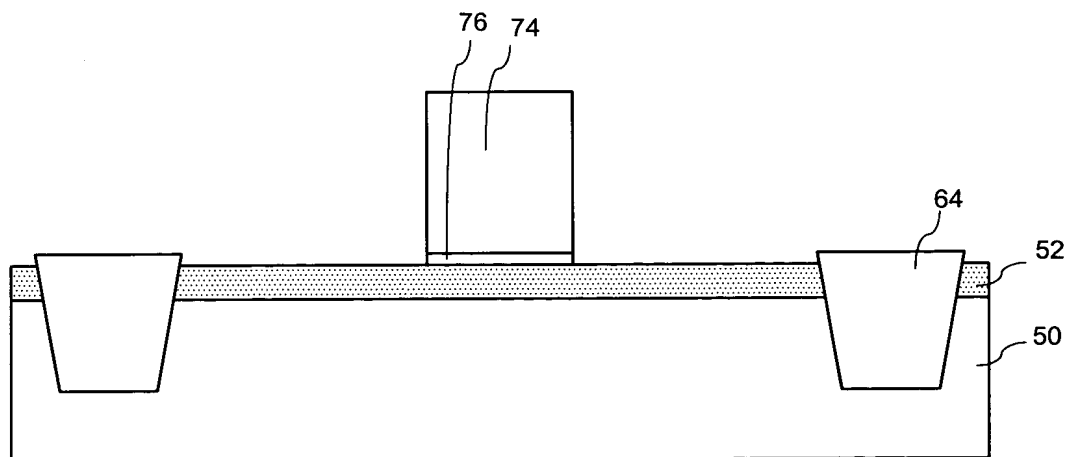


Figure 3f

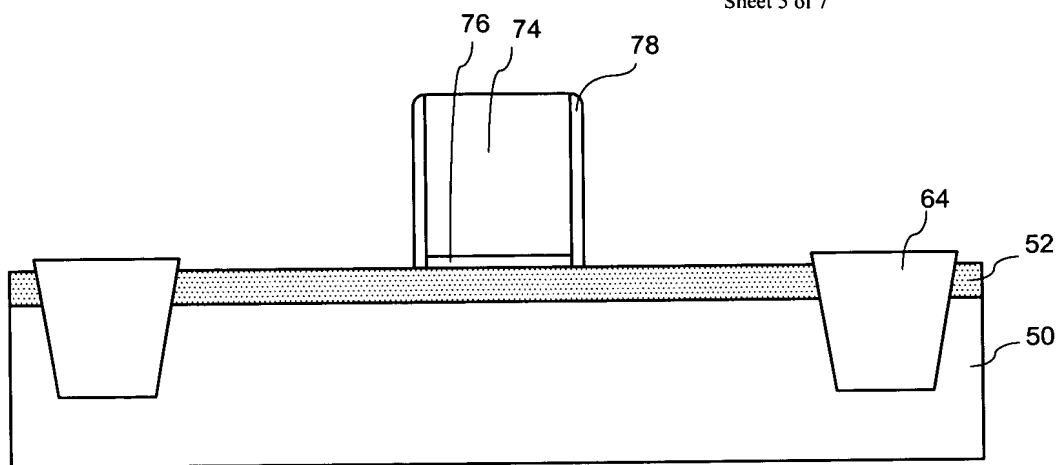


Figure 3g

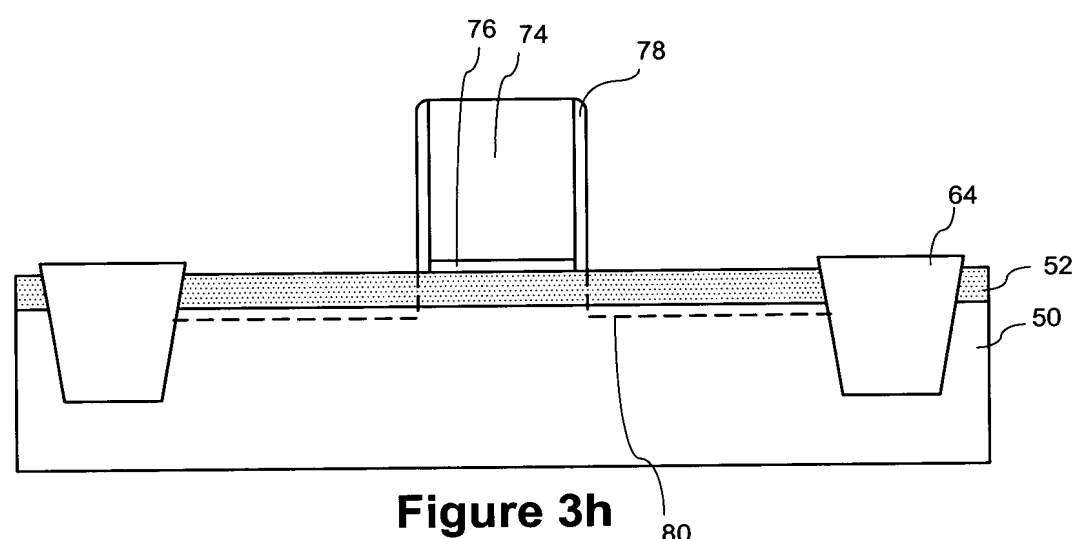


Figure 3h

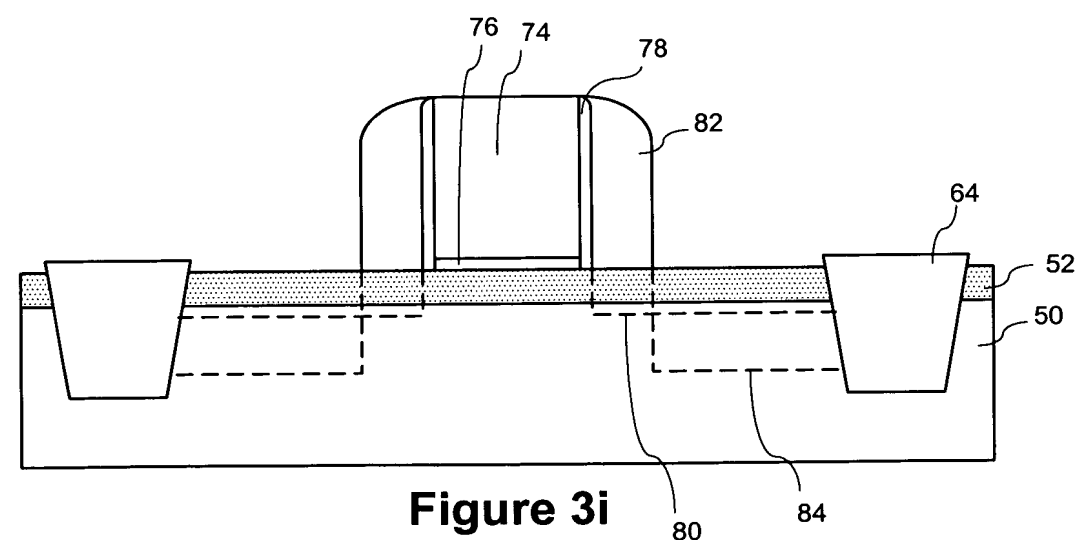


Figure 3i

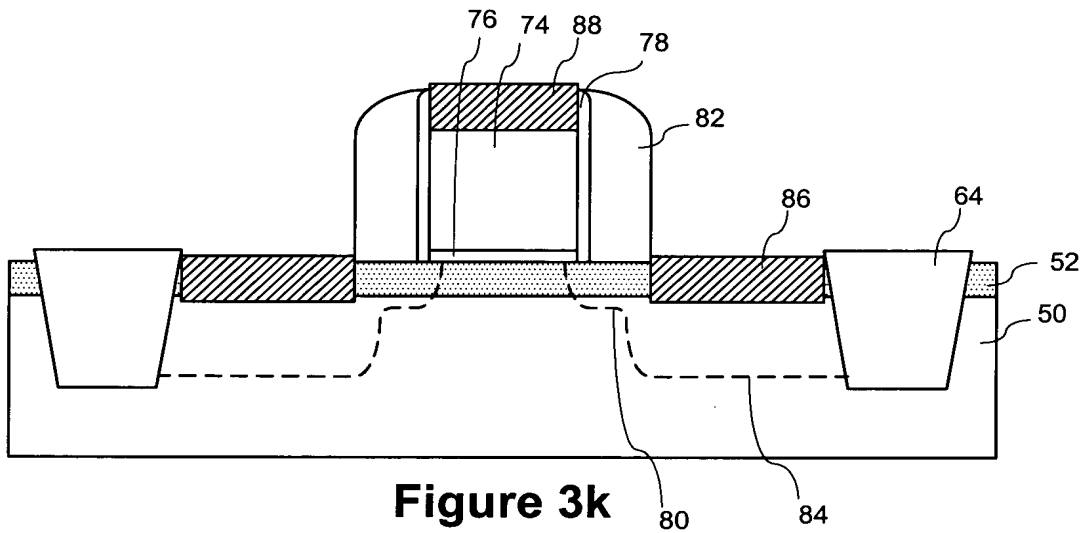
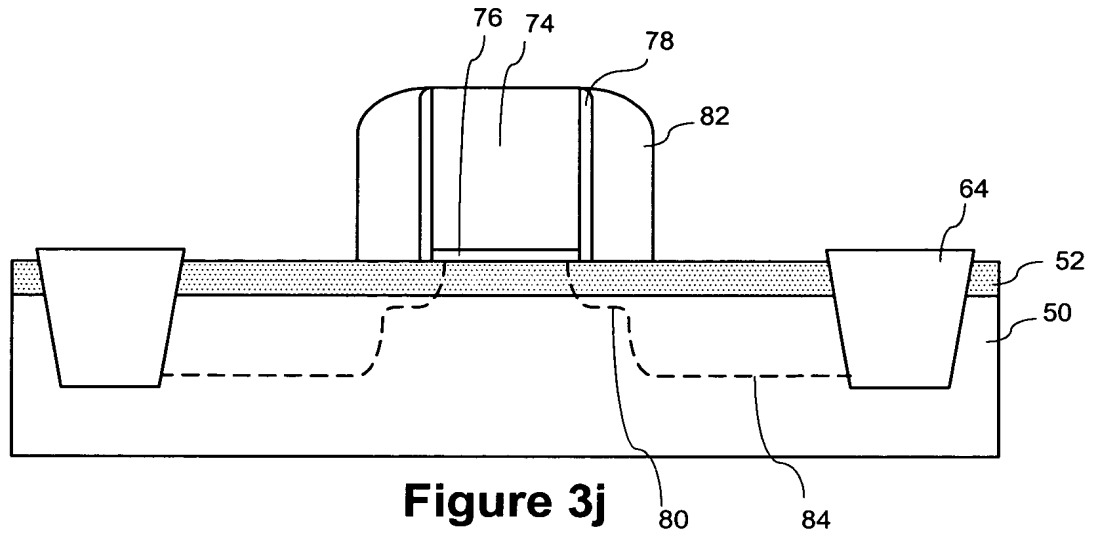
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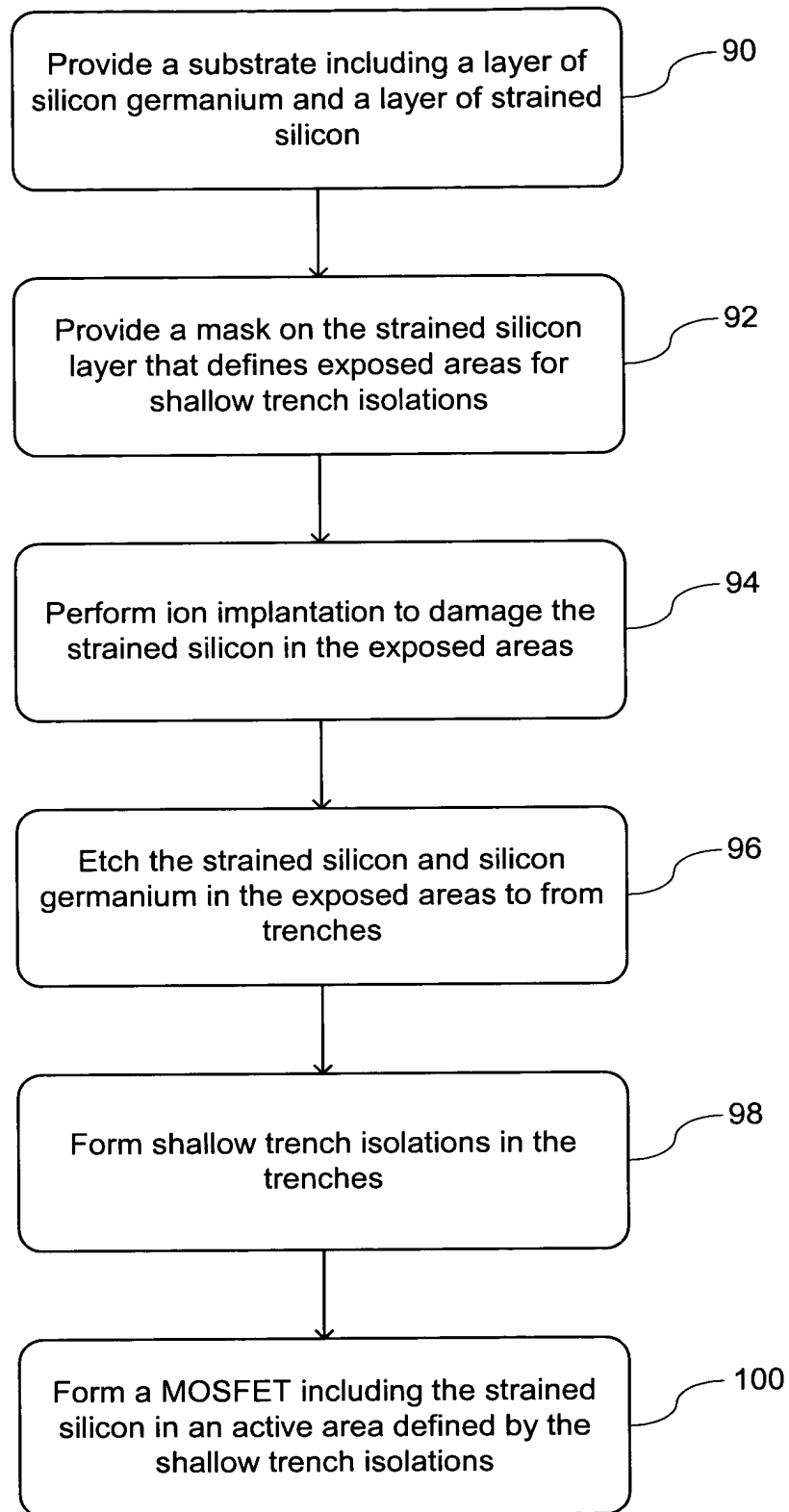


Figure 4